

Performance

- Technical: 0.25um GaN HEMT
- Frequency: 13.7-14.5GHz
- Typical Output Power: 47.0dBm (CW)
- Typical Power Gain: 6dB
- PAE: 30%
- Bias Voltage: 28V/0.6A
- Size: 21.3*13.1*5.2mm

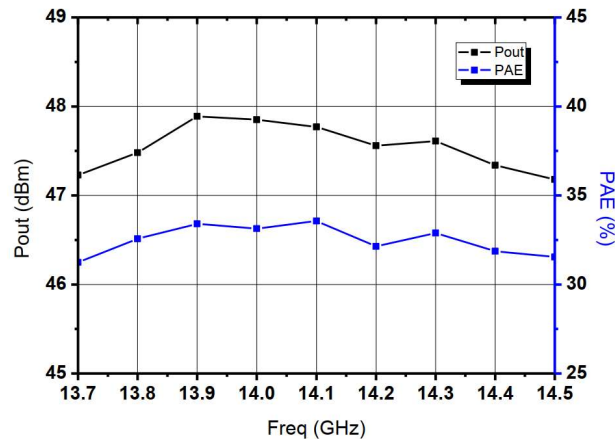


Electrical Specifications (Ta=25°C, Vd=28V, Id≈0.6A, F: 13.7~14.5GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Power Output	46.5	47	-	dBm
Gp	Power Gain	5.5	6	-	dB
η_{add}	Power Added Efficiency	-	30	-	%
Rth	Thermal Resistance	-	-	1.5	°C/W

Test Curves (Ta=25°C)

Output Power/PAE & Frequency

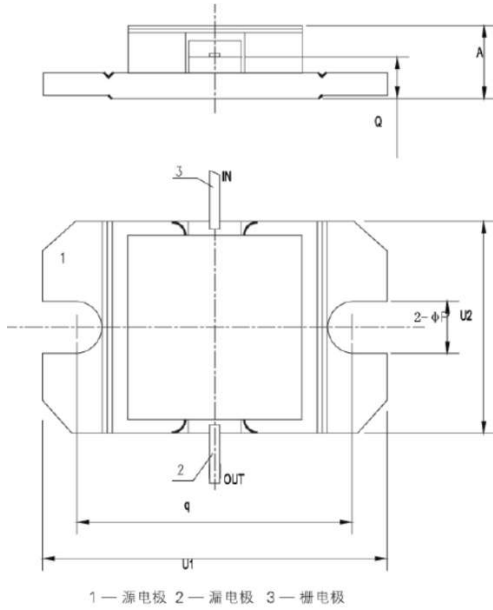


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vds	Drain Source Voltage	32V	
Vgs	Gate Source Voltage	-5V	
Pd	DC Power	80W	25°C
Tch	Channel Temperature	225°C	
Tm	Mounting Temperature	300°C	1min, N2 protection
Tstg	Storage Temperature	-55~175°C	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Symbol	Value (mm)		
	Min.		Max.
A	-	-	5.2
Q	2.50	-	2.80
q	16.80	-	17.20
U1	20.80	-	21.30
U2	12.85	-	13.10
Øp	3.10	-	3.40

Application Circuit

